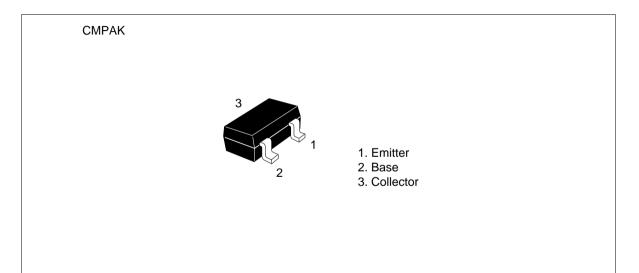
Silicon NPN Epitaxial

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Application

UHF / VHF wide band amplifier

Outline





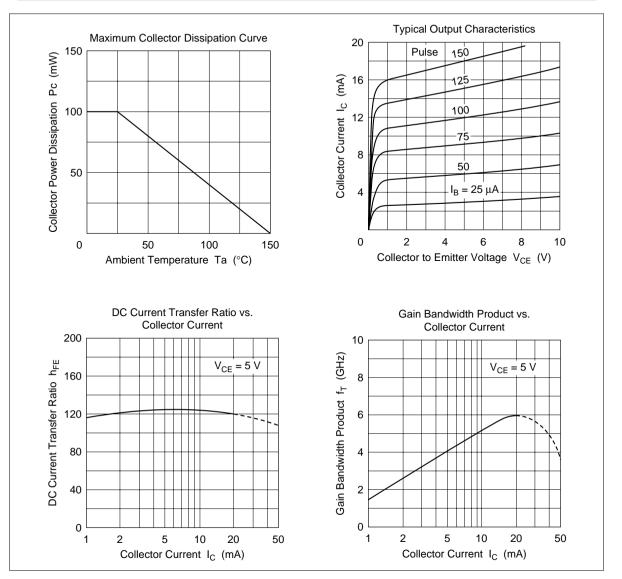
Absolute Maximum Ratings ($Ta = 25^{\circ}C$)

Item	Symbol	Ratings	Unit	
Collector to base voltage	V _{CBO}	15	V	
Collector to emitter voltage	V _{CEO}	V _{CEO} 11		
Emitter to base voltage	V _{EBO}	2	V	
Collector current	Ι _c	50	mA	
Collector power dissipation	Pc	100	mW	
Junction temperature	Тј	150	°C	
Storage temperature	Tstg	-55 to +150	°C	

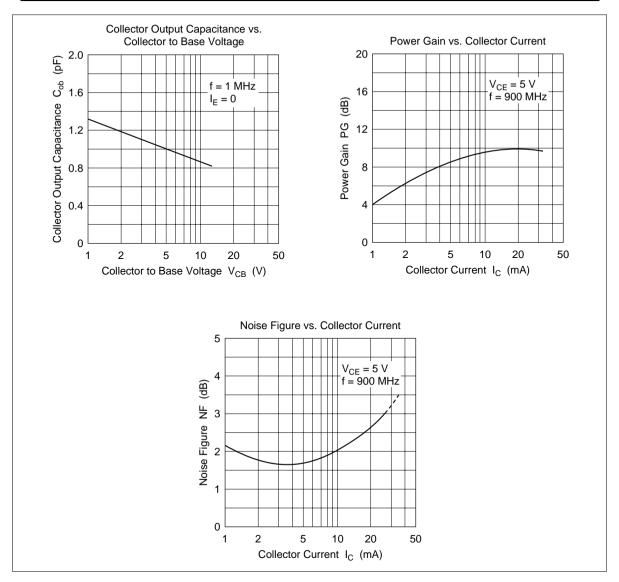
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	$V_{(BR)CBO}$	15	_	_	V	$I_{c} = 10 \ \mu A, \ I_{E} = 0$
Collector cutoff current	I _{CBO}	_		1	μΑ	$V_{CB} = 12 \text{ V}, \text{ I}_{E} = 0$
Collector cutoff current	I _{CEO}	—	—	1	μA	$V_{ce} = 10 \text{ V}, \text{ I}_{e} = \infty$
Emitter cutoff current	I _{EBO}	—		1	μΑ	$V_{EB} = 1 V, I_{C} = 0$
DC current transfer ratio	h_{FE}	50	120	250	—	$V_{ce} = 5 \text{ V}, \text{ I}_{c} = 20 \text{ mA}$
Collector output capacitance	Cob	_	1.0	1.5	pF	$V_{CB} = 5 \text{ V}, \text{ I}_{E} = 0,$ f = 1MHz
Gain bandwidth product	f _⊤	4.5	6.0	—	GHz	$V_{ce} = 5 \text{ V}, \text{ I}_{c} = 20 \text{ mA}$
Power gain	PG	_	10	_	dB	$V_{ce} = 5 \text{ V}, \text{ I}_{c} = 20 \text{ mA},$ f = 900 MHz
Noise figure	NF	_	1.6		dB	$V_{ce} = 5 \text{ V}, \text{ I}_{c} = 5 \text{ mA},$ f = 900 MHz

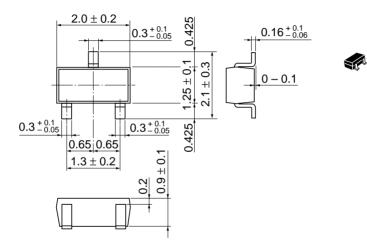
Note: Marking is "IS-".



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Unit: mm



Hitachi Code	CMPAK
JEDEC	
EIAJ	Conforms
Weight (reference value)	0.006 g

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